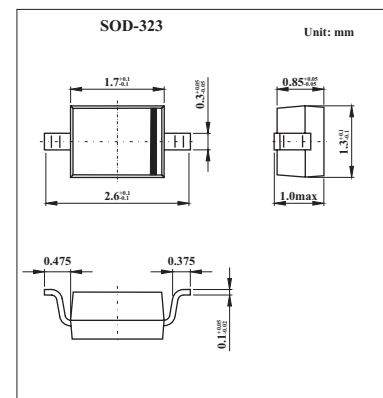


Silicon Epitaxial Planar Pin Diode

HVU132

■ Features

- Low capacitance. (C=1.0pF max)
- Low forward resistance. ($r_f=0.7\ \Omega$ max)

■ Absolute Maximum Ratings $T_a = 25\ ^\circ\text{C}$

| Parameter | Symbol | Value | Unit |
|----------------------|-----------|-------------|------------------|
| Peak reverse voltage | V_{RM} | 65 | V |
| Reverse voltage | V_R | 60 | V |
| Forward current | I_F | 100 | mA |
| Power dissipation | P_d | 150 | mW |
| Junction temperature | T_j | 125 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +125 | $^\circ\text{C}$ |

■ Electrical Characteristics $T_a = 25\ ^\circ\text{C}$

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|--------------------|--------|--|-----|-----|-----|----------|
| Reverse current | I_R | $V_R = 60\ \text{V}$ | | | 0.1 | nA |
| Forward voltage | V_F | $I_F = 10\ \text{mA}$ | | | 1.0 | V |
| Capacitance | C | $V_R = 1\ \text{V}, f = 1\ \text{MHz}$ | | | 0.5 | pF |
| Forward resistance | r_f | $I_F = 10\ \text{mA}, f = 100\ \text{MHz}$ | | | 2.0 | Ω |

■ Marking

| Marking | P2 |
|---------|----|
| | |